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INFORMATION DISCLOSURE
STATEMENT B PAPPLICANT
(Use as many sheets as necessary) MAR 2 4 2003 Sheet 1 of 1

Application Number	09/883795	
Filing Date	June 18, 2001	
First Named Inventor	Forbes, Leonard	
Group Art Unit	2814	
Examiner Name	Theresa T. Doan	

Attorney Docket No: 303.355US4

		US P	ATENT DOCUMENT	S		
Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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		FOREIGN PATENT	DOCUMENTS			
Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T ²

Examiner Cite No 1		R DOCUMENTS NON PATENT LITERATURE DOCUMENTS Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.				
7()		BELTRAM, F., et al., "Memory phenomena in heterojunction structures: Evidence for suppressed thermionic emission", <u>Appl. Phys. Lett., 53(5)</u> , (1988),pp. 376-378				
TD		LOTT, J., et al., "Anisotropic thermionic emission of electrons contained in GaAs/AlAs floating gate device structures", <u>Appl. Phys. Lett., 55(12)</u> , (1989),pp. 1226-1228				
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